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The invention relates to a nanostructured materials production technology, in particular to processes for producing nanostructures by electrochemical processing.

The process for producing wide-gap band semiconductor nanowires on narrow-gap band semiconductor substrates, according to the invention, comprises anodizing the surface of a semiconductor substrate. At the same time, the nanowires obtained as a result of anodization are subjected to heat treatment in an inert atmosphere with a low oxygen content.

Claims: 1

Fig.: 5